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Innovative Silicon, Inc. named a top finalist in Swiss Economic Forum Awards

Z-RAM floating body memory technology, a leading DRAM replacement, enables continued electronics industry progress on Moore's Law path

SANTA CLARA, Calif. — May 28, 2008 — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory technology, today announced that it was one of the top finalists in the Swiss Economic Forum's 2008 Awards. Now in its 10th year, the Swiss Economic Forum is a two-day gathering of 1200 leading figures from industry, commerce, politics and academia. Held on May 22 and 23 in Thun, Switzerland, the event provided a discussion forum for international business, technology and economic trends.

The awards celebrate success in companies that have been in business for six or less years, and focus on innovation, product development, entrepreneurial enterprise, job creation and financial achievement. ISi was named a finalist in the High Tech/Biotech category.

"We are delighted to have been chosen as a leading finalist in these prestigious awards," commented ISi's CEO, Mark Eric Jones. "Low cost, efficient DRAM memories are a key enabling technology for new electronic product designs, and are therefore fundamental for continued economic development."

The electronics industry is now at a crossroads: traditional memory technologies are no longer shrinking as predicted by Moore's Law, which is slowing down the progress many have come to expect in the electronics industry. Chip makers must choose new approaches that enable them to break through this memory 'brick wall' and continue delivering better performance at lower prices.

"Our Z-RAM floating body memory technology has emerged as a leading DRAM replacement candidate, having already been licensed by both Hynix Semiconductor and AMD for their future product designs," continued Jones. "Z-RAM will help the industry continue delivering smaller,

lower cost and higher performing products.”

About Innovative Silicon

Innovative Silicon, Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world’s lowest-cost semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World Economic Forum’s selection of ISi as a 2008 Technology Pioneer, and IEEE Spectrum Magazine’s selection of Z-RAM as the 2007 “Emerging Technology Most Likely to Succeed.” Z-RAM is a “Zero Capacitor,” true single-transistor floating body memory that eliminates the complex capacitor found in today’s DRAM technologies – a fundamental roadblock to Moore’s Law of scaling. Z-RAM provides semiconductor manufacturers a solution for nano-scale manufacturing processes that can dramatically lower semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling \$47 million, received over 25 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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